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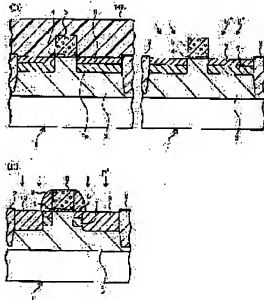
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(54) SEMICONDUCTOR DEVICE AND ITS MANUFACTURING METHOD

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a semiconductor device capable of forming a pocket area by using indium and decreasing the increase of leak current by ion injection of indium.

SOLUTION: The semiconductor device has first and second active areas demarcated on the main surface of a silicon substrate, a first n channel MOS transistor formed on the first active area having a first extension area and a first pocket area adding the indium of first concentration at a position deeper than the first extension area, and a second n channel MOS transistor formed on the second active area having a second extension area and a second pocket area adding the indium of second concentration lower than the first concentration at another position deeper than the second extension area. Furthermore, boron may be ion-injected in the second pocket area.



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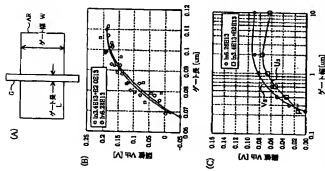
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【特許補正2】

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【発明者】

【特許補正1】

【特許補正対象項名】図5

【特許補正対象項名】図4

【特許補正】変更

【特許内容】

【図4】

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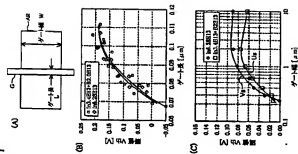
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【特許方法】変更

【特許内容】

【図8】



Fターム(参考) 5F06B A07 A08 A803 A01 B401

B605 B608 B616 B618 B625

B608 B609 B614

5F14B A43 A22 A24 A50 A803

A52 A53 B601 B615 B626

B67 B69 B71 B78 B606

B672 B653 B653 B614 B615

B671 B606 B602 B613 B614

B671 B622 B604 B608